



BC847PN

COMPLEMENTARY PAIR SMALL SIGNAL TRANSISTOR IN SOT363

Features

- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

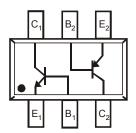
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.006 grams (approximate)





Top View



Device Schematic Top View

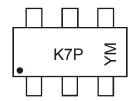
Ordering Information (Note 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847PN-7-F	AEC-Q101	K7P	7	8	3,000
BC847PN-13-F	AEC-Q101	K7P	13	8	10,000
BC847PN-7R-F	AEC-Q101	K7P	7	8	3,000
BC847PNQ-7-F	Automotive	K7P	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K7P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2010	201	1	2012	20	13	2014	2	2015	2016		2017
Code	X	Y		Z		A	В		С	D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings: NPN, BC847B Type (Q₁) (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	Ic	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Emitter Current	I _{EM}	200	mA

Absolute Maximum Ratings: PNP, BC857B Type (Q2) (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	Ic	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Emitter Current	I _{EM}	-200	mA

Thermal Characteristics – Total Device (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	P_{D}	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Note:

Thermal Characteristics - Total Device

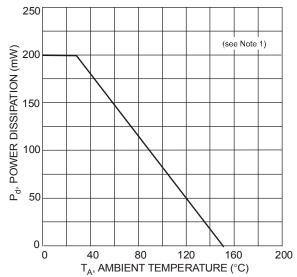


Fig. 1, Power Derating Curve (Total Device)

^{6.} For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.



Electrical Characteristics: NPN, BC847B Type (Q₁) (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 7)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	-	V	$I_C = 100 \mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	$I_E = 100 \mu A, I_C = 0$
DC Current Gain	h _{FE}	200	290	450	_	$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	90 200	250 600	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	1	700 900	1	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Voltage	V _{BE(on)}	580 —	660 —	700 720	mV	$V_{CE} = 5.0V, I_{C} = 2.0mA$ $V_{CE} = 5.0V, I_{C} = 10mA$
Collector-Cutoff Current	I _{CBO}		_	15 5.0	nΑ μΑ	V _{CB} = 30V V _{CB} = 30V, T _A = +150°C
Gain Bandwidth Product	f _T	100	300	_	MHz	$V_{CE} = 5.0V, I_{C} = 10mA,$ f = 100MHz
Collector-Base Capacitance	C _{CBO}	_	3.5	6.0	pF	V _{CB} = 10V, f = 1.0MHz
Noise Figure	NF	ı	2.0	10	dB	$V_{CE} = 5V, I_{C} = 200\mu A,$ $R_{G} = 2.0k\Omega, f = 1.0kHz,$ $\Delta f = 200Hz$

Note: 7. Short duration pulse test used to minimize self-heating effect.

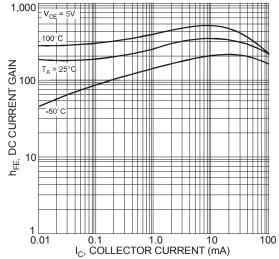


Figure 2. Typical DC Current Gain vs. Collector Current (BC847B Type)

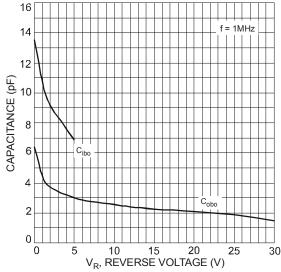


Figure 4. Typical Capacitance Characteristics (BC847B Type)

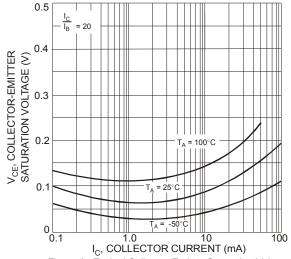


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC847B Type)

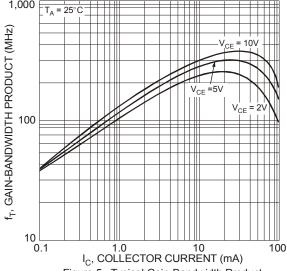


Figure 5. Typical Gain-Bandwidth Product vs. Collector Current (BC847B Type)



Electrical Characteristics: PNP, BC857B Type (Q₂) (@T_A = +25°C unless otherwise specified.)

Characteristic (Note 8)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_	_	V	$I_C = -100 \mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	-	-	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	_	_	V	$I_E = -100 \mu A, I_C = 0$
DC Current Gain	h _{FE}	220	290	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-75 -250	-300 -650	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$ $I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	-	-700 -850	— -950	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$ $I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Voltage	V _{BE(on)}	-600 —	-650 —	-750 -820	mV	V_{CE} = -5.0V, I_{C} = -2.0mA V_{CE} = -5.0V, I_{C} = -10mA
Collector-Cutoff Current	I _{CBO}	_	_	-15 -4.0	nΑ μΑ	V _{CB} = -30V V _{CB} = -30V, T _A = +150°C
Gain Bandwidth Product	f _T	100	200	ı	MHz	$V_{CE} = -5.0V, I_{C} = -10mA,$ f = 100MHz
Collector-Base Capacitance	C _{CBO}		3	4.5	pF	$V_{CB} = -10V, f = 1.0MHz$
Noise Figure	NF			10	dB	V_{CE} = -5V, I_C = -200 μ A, R_G = 2.0k Ω , f = 1.0kHz, Δ f = 200Hz

Note: 8. Short duration pulse test used to minimize self-heating effect.

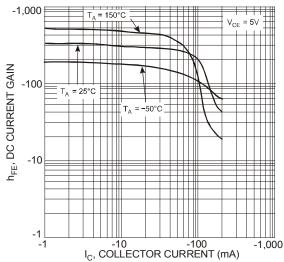


Figure 6. Typical DC Current Gain vs. Collector Current (BC857B Type)

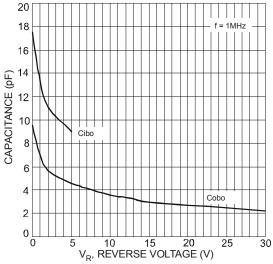


Figure 8. Typical Capacitance Characteristics (BC857B Type)

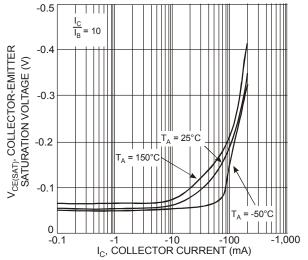


Figure 7. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC857B Type)

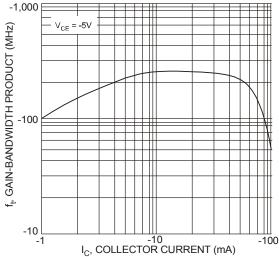
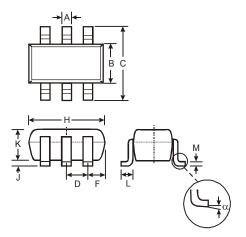


Figure 9. Typical Gain-Bandwidth Product vs. Collector Current (BC857B Type)



Package Outline Dimensions

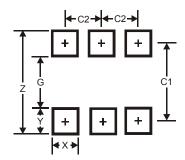
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT363								
Dim	Min	Min Max							
Α	0.10	0.30	0.25						
В	1.15	1.35	1.30						
C	2.00	2.20	2.10						
D	0.65 Typ								
F	0.40	0.45	0.425						
Н	1.80	2.20	2.15						
J	0	0.10	0.05						
K	0.90	1.00	1.00						
L	0.25	0.40	0.30						
M	0.10	0.22	0.11						
α	0°	8°	-						
All	All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65



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